

**Notice of References Cited**Application/Control No.  
10/529,425Applicant(s)/Patent Under  
Reexamination  
LAMMEL ET AL.Examiner  
George A. GoudreauArt Unit  
1763

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*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
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*	B	US-2004/0065931	04-2004	Benzel et al.	257/414
*	C	US-5,594,171	01-1997	Ishida et al.	73/514.32
*	D	US-6,197,655	03-2001	Montanini et al.	438/411
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	L	US-			
	M	US-			

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	N	2001-019,723	03-2001	WO	Lammel	-----
	O	2004-028,956	12-2004	WO	Lammel	-----
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**NON-PATENT DOCUMENTS**

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)			
	U	"A new wide-dimensional freestanding microstructure fabrication technology using laterally formed porous silicon as sacrificial layer"; Sensors and Actuators; vol. 84; 2000; Lee et. al.; pp. 181-185			
	V	"Thick porous silicon formation using implanted mask technology"; Sensors and Actuators; vol. 76; 2000; Splinter et. al.; pp.354-360			
	W				
	X				

\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.